The upgrade of the CMS hadron calorimeter with silicon photomultipliers

Nadja Strobbe on behalf of the CMS collaboration

TWEPP 2016





Introduction: CMS HCAL



Introduction: CMS HCAL

HCAL = hadron calorimeter

- 17 layers of brass absorber and scintillator tiles in barrel (HB) and endcap (HE) sections
- Wavelength-shifting fibers transport scintillation light
 RING 2
- Currently using
 Hybrid Photo Diodes
 (HPD) to collect light from scintillator
- **QIE8** ASIC to integrate and digitize signal from HPDs
- Limited depth segmentation

 (1 3 depths)





Motivation for upgrade

- Higher than expected radiation damage to scintillator tiles resulting in increased signal loss
- Radiation damage "dose rate model" arxiv:1608.07267
 - signal loss depends exponentially on accumulated dose, with decay constant D depending on dose rate: ~exp(-dose/D[Mrad])
 - Less damage for higher dose rate
 - Caused by chemical effects related to oxygen diffusion



Motivation for upgrade

- Effect of radiation damage can be mitigated by replacing HPDs with Silicon PhotoMultipliers (SiPMs):
 - 3x photon detection efficiency (PDE) → increase signal size

 - Recovers performance for physics quantities such as ET^{miss} and jet energy resolution



Overview of upgraded system

- First large installation of SiPMs in a radiation environment (1x10¹² 1MeV neutrons/cm²)
- Upgraded HE frontend (~7k channels) to be installed early 2017, upgraded HB frontend (~9.2k channels) to be installed during LHC LS2 (2019)



Frontend overview



RM: readout module **CU**: calibration unit with LED **CCM**: clock, control & monitoring

Readout box schematic



Readout module schematic



SiPMs

- Produced by Hamamatsu
- 4500 pixels/mm2, each pixel is operated in Geiger mode, signal is sum of all fired pixels
- 2 sizes: 2.8 mm and 3.3 mm diameter to handle varying number of layers that are added together
- Fast recovery time of 10 ns

 → effective pixel count increases
 by factor of ~3
- 8 SiPMs in one package
- Increase in dark current after irradiation is well-understood and at manageable level





SiPMs

Advantages compared to HPDs:

- Smaller size
- Operate at much lower voltage (~70V vs ~8000V) and have no magnetic field sensitivity
 - → avoid high-energy anomalous noise present with HPDs
- Better photon detection efficiency, ~30%
- Very high gain, factor 150-200 larger than HPDs, depending on operating point



SiPM control electronics

Goal: achieve SiPM gain stability and accuracy to within 1% Infrastructure needed:

- 1. Precise bias voltage control
- 2. Precise temperature control (~2%/°C gain sensitivity)

Bias voltage (BV) control

- Generate bulk BV from backplane power
- Step down to operational voltage for each SiPM individually

Peltier cooling

- run SiPMs at 5°C
- online control loop via slow controls to monitor and adjust
- temperature sensor next to SiPMs
- 12-bit DAC resulting in 0.01°C control precision

SiPM control electronics

BV converter board

- mounted on control board
- custom boost converter:
 9.5V on backplane → O(100V)

Control board:

- bulk BV stepped down to ~70V
 - separately per channel
 - 20 mV LSB (1% precision on gain for $V-V_b = 3V$)
 - 3-7 mV ripple/noise
- 1 control board per RM (i.e. 48 SiPM channels)
- measures SiPM leakage current
- measures temperature and humidity



SiPM control electronics

Quality control of all produced cards

- Checked response of all BV channels to the set DAC value
- Very uniform out of the box: RMS of 0.3%
- Small variations will be further leveled to achieve uniform SiPM gain across all channels



SiPM mounting board

- Rigid-flex construction
 - Rigid part holds the SiPMs inside cooling assembly
 - Flex cables interface with QIE chips for charge integration
 - Flex cable to transfer BV to each SiPM
- Temperature and humidity sensors installed next to SiPMs
- Worked with vendor
 - Optimize fabrication process
 - Design adjusted to allow more reliable production



QIE cards



QIE11 ASIC

- Integrate charge in 25ns intervals without dead time
- 17-bit dynamic range with 8-bit readout, previous generation (QIE8) had 14-bit dynamic range with 7-bit readout.
- Extended dynamic range (350 pC with 3 fC LSB) with extra bit of precision to match the larger SiPM gain
- Achieves ~1% resolution over full dynamic range by using 4 integration ranges (scaled by factors of 8) with a 6-bit pseudo-logarithmic ADC in each range
- Programmable current shunt (between 1 and 1/11.5) for tuning SiPM gain independently of SiPM PDE



QIE11 testing

- O(40k) chips have been thoroughly tested before mounting on QIE cards
- Custom test setup
 - Robot system for moving QIE chips onto test board
 - Can load 1120 chips
 per cycle
 - Test suite covers all aspects of the chips, and takes about 2.5 minutes per chip.



QIE11 testing

- Very good acceptance:
 - 98% for basic functionality
 - 86% for final selection, including uniformity selections



QIE card testing

- All cards went through quality control (94% yield)
- Each QIE on each card has been calibrated for all shunt values using a custom charge injector board





Testbeam

- Preproduction system was tested at the CERN H2 beamline (muon and pion beam)
- Shows excellent performance of SiPMs vs HPDs in terms of signal to noise ratio
- 4% RMS on SPE charge using uniform bias voltage setting, at constant over-voltage this becomes 1%



Summary

- CMS HCAL will upgrade the frontend with SiPMs and associated readout and control electronics
- Upgrade for endcap HCAL is planned for early 2017 and final testing and burn-in of the new system is well underway
- Upgrade of barrel HCAL will be done during LS2